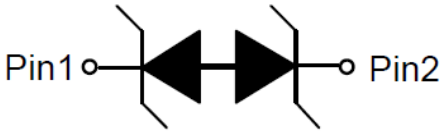
Description

The XE2XLC5VB is a bi-directional ESD protection diode designed to protect sensitive electronic components which are connected to low speed data lines and control lines from over-stress caused by ESD (Electrostatic Discharge), EFT (Electrical Fast Transients) and Lightning. The XE2XLC5VB may be used to provide ESD protection up to ±15kV contact and ±20kV air discharge according to IEC61000-4-2, and withstand peak pulse current up to 2A (8/20μs) according to IEC61000-4-5.
The XE2XLC5VB is available in DFN0603-2L package. Standard products are Pb-free and Halogen-free.

http//:www.xihangsemi.com

DFN0603-2L



Circuit Diagram

Features

- Working voltage: 5V
- DFN0603-2L Package
- Transient protection for data lines to
  IEC61000-4-2 (ESD) ±20kV (air),
  ±15kV (contact)
  IEC61000-4-5 (Surge) 2A (8/20us)
  IEC61000-4-4(EFT)40A(5/50ns)
- Low leakage current
- Low clamping voltage
- Solid-state silicon-avalanche technology

3L

Marking（Top View）

Order Information

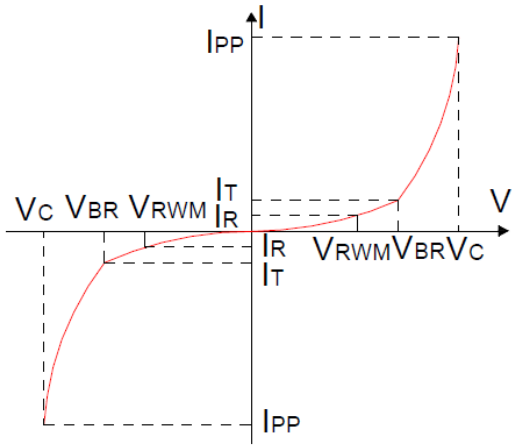
Device	Package	Shipping
XE2XLC5VB	DFN0603-2L	10000/Tape&Reel

Applications

- Personal digital assistants (PDA's)
- Notebooks, Desktops, and Servers
- Cell phone Handsets and Accessories
- Portable Electronics
- Peripherals

Definitions of electrical characteristics

Symbol	Parameter
V_{RWM}	Reverse Stand-off Voltage
I_R	Reverse Leakage Current @ V_{RWM}
V_{BR}	Reverse Breakdown Voltage @ I_T
I_R	Reverse Breakdown Current
I_{PP}	Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_{PP}



Absolute Maximum Rating

Rating	Symbol	Value	Units
Peak Pulse Power (t_P = 8/20μS)	P_{PK}	26	W
Peak Pulse Currentr (t_P = 8/20μS)	I_{pp}	2	A
ESD according to IEC61000-4-2 air discharge	V_{ESD}	±20	kV
ESD according to IEC61000-4-2 contact discharge		±15	kV
Lead Soldering Temperature	T_L	260 (10 sec)	℃
Operating Temperature	T_{OP}	-55 to +125	℃
Storage Temperature	T_{STG}	-55 to +150	℃

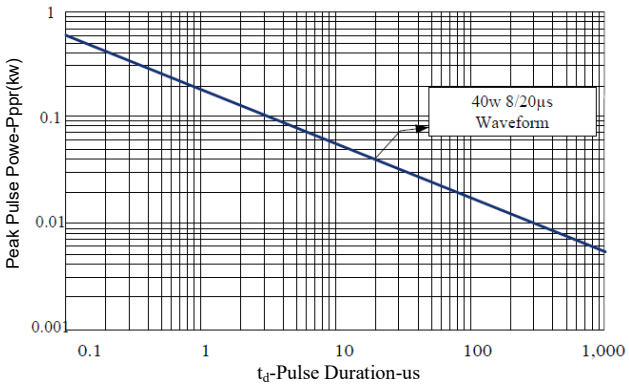
Electrical Characteristics (Ta=25℃, unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Units
Reverse Stand-off Voltage	V_{RWM}				5	V
Reverse Leakage Current	I_R	V_{RWM} =5V			100	nA
Reverse Breakdown Voltage	V_{BR}	I_T=1mA	5.6			V
Clamping Voltage	V_C	I_{PP}=2A t_P = 8/20μs		11	13	V
Junction Capacitance	C_j	V_R=0V f = 1MHz		3	3.5	pF

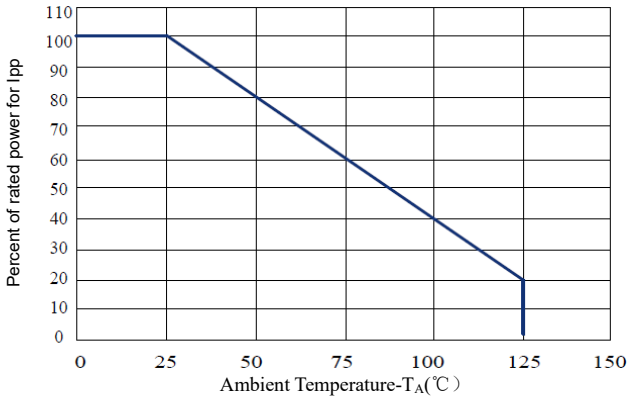
Notes:

1)Non-repetitive current pulse, according to IEC61000-4-5.

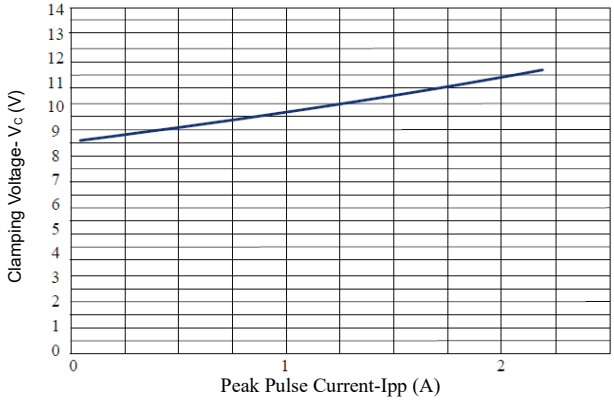
Typical Characteristics (Ta=25℃, unless otherwise noted)



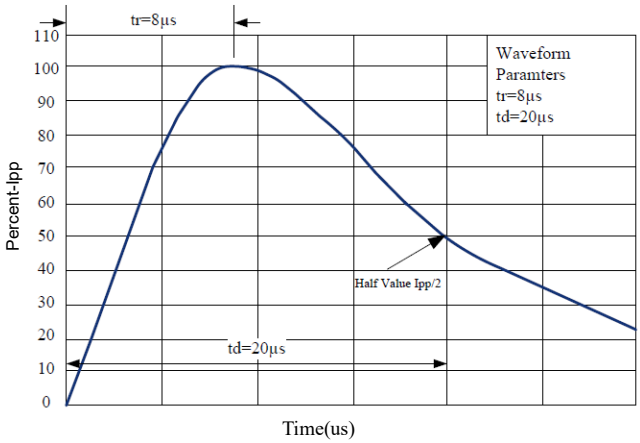
Peak Pulse Power vs.Pulse Time



Power Derating Curve

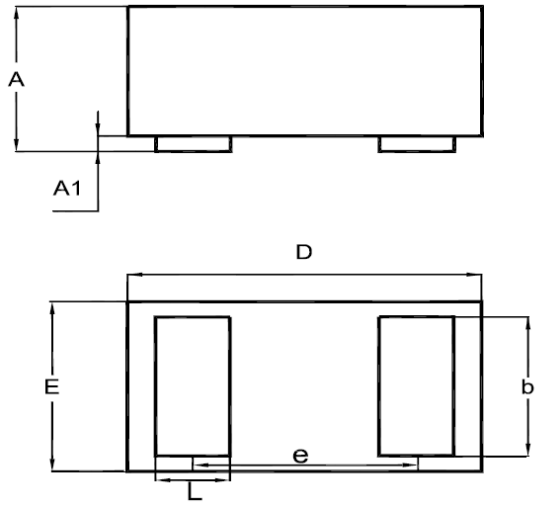


Clamping Voltage vs. Peak Pulse Current



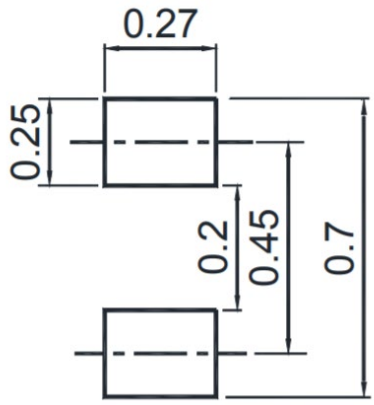
Pulse Waveform

Package Outline Dimensions (DFN0603-2L）

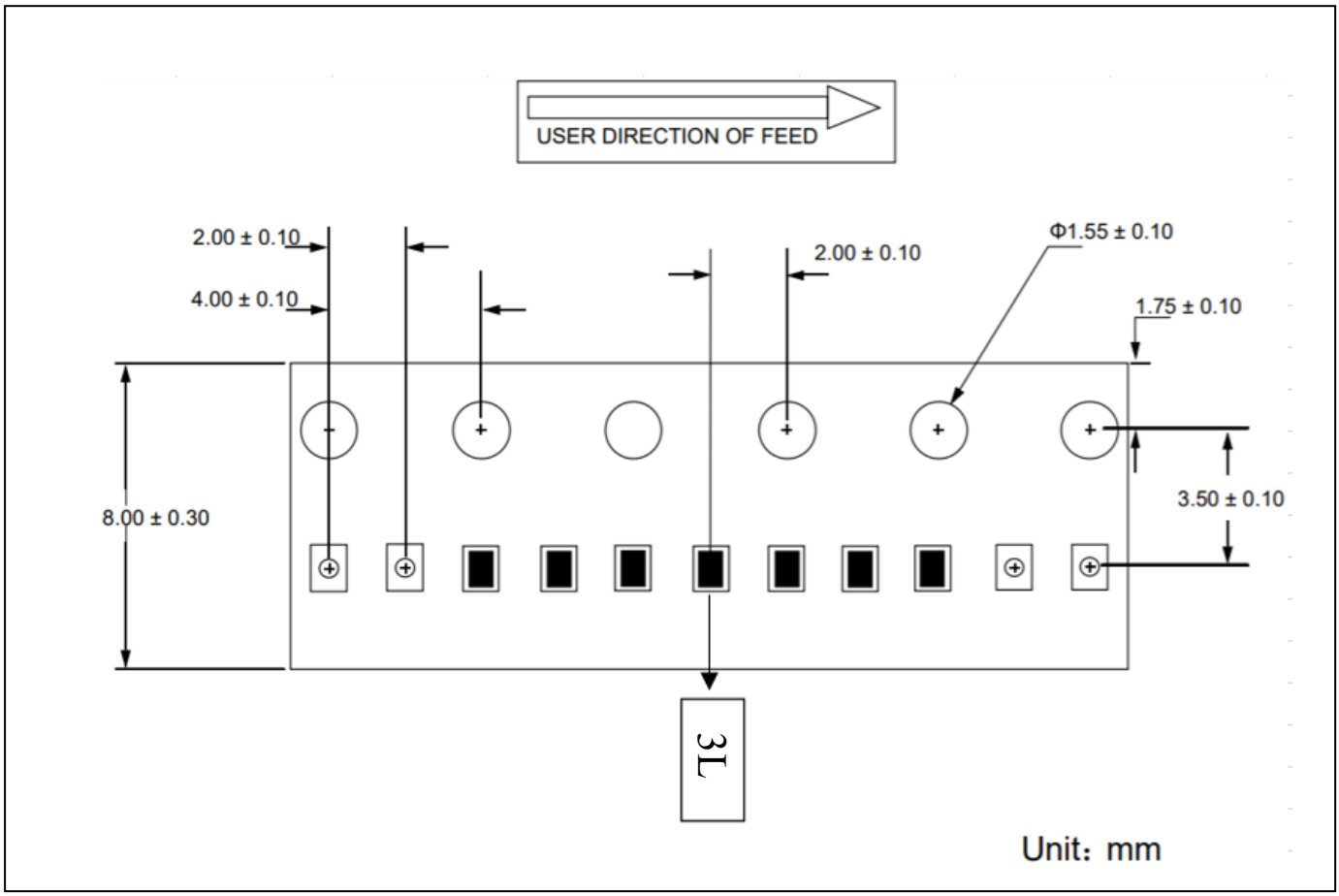


UNIT	A	A1	b	D	E	e	L
mm	0.27 0.33	0 0.025	0.21 0.29	0.57 0.65	0.28 0.35	0.355	0.14 0.22

Recommend Land Pattern (Unit: mm)



Note:
This recommended land pattern is for reference purpose only.



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